MJ N-Channel Enhancement Mode Power MOSFET

Description

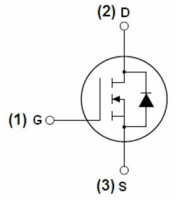
The MJ3035Q uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

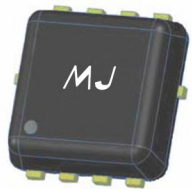
- V_{DS}=30V,I_D=35A
  $R_{DS(ON)}$<7mΩ @ V_{GS}=10V
  $R_{DS(ON)}$<11mΩ @ V_{GS}=4.5V
- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

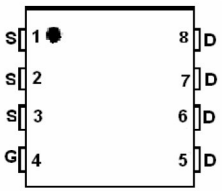
- Secondary side synchronous rectifier
- High side switch in POL DC/DC converter



Schematic diagram



Marking and pin assignment



DFN 3x3 EP top view

100% UIS TESTED! 100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
MJ3035Q	MJ3035Q	DFN 3x3 EP	-	-	-

Absolute Maximum Ratings (T_C =25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	35	A
Pulsed Drain Current	I_{DM}	120	A
Maximum Power Dissipation	P_D	35	W
Single pulse avalanche energy (Note 5)	E_{AS}	150	mJ
Derating factor		0.28	W/℃
Operating Junction and Storage Temperature Range	T_J ,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case (Note 2)	$R_{\theta JA}$	3.6	℃/W

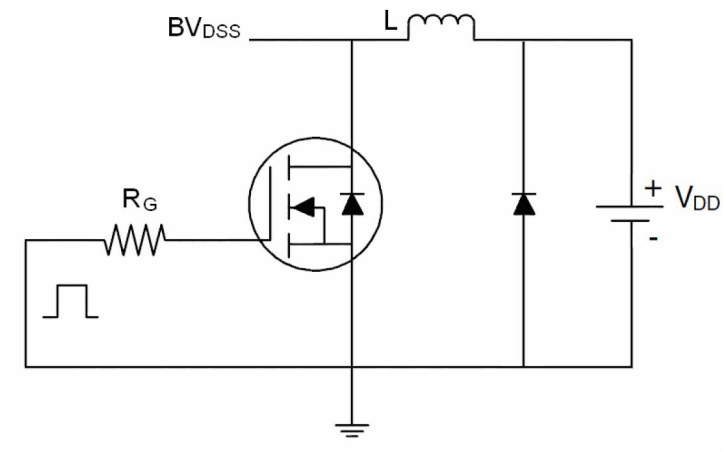
Electrical Characteristics (T_A =25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	30	33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{DS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} =V_{GS} ,I_D =250μA	1	1.6	3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS} =10V, I_D =12A	-	6.5	7.0	mΩ
		V_{GS} =4.5V, I_D =10A	-	9	11	mΩ
Forward Transconductance	g_{FS}	V_{DS} =10V,I_D =12A	30	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{lss}	V_{DS}=15V,V_{GS}=0V, F=1.0MHz	-	2330	-	PF
Output Capacitance	C_{oss}		-	460	-	PF
Reverse Transfer Capacitance	C_{rss}		-	230	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=15V,I_D=12A V_{GS}=10V,R_{GEN}=6Ω	-	18	-	nS
Turn-on Rise Time	t_r		-	10	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	34	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	V_{DS}=15V,I_D=12A, V_{GS}=10V	-	45	-	nC
Gate-Source Charge	Q_{gs}		-	9.4	-	nC
Gate-Drain Charge	Q_{gd}		-	7.7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=12A	-	0.85	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	35	A
Reverse Recovery Time	t_{rr}	T_J=25°C, I_F=12A di/dt=100A/μs (Note 3)	-	-	47	nS
Reverse Recovery Charge	Q_{rr}		-	-	25	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible(turn-on is dominated by LS+LD)				

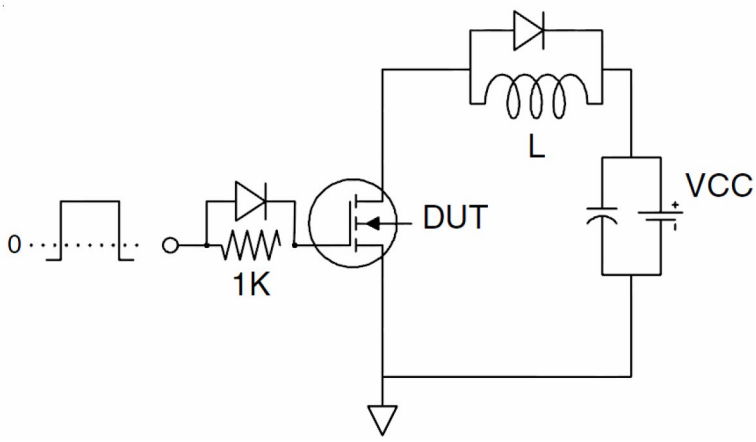
Notes:

① Repetitive Rating: Pulse width limited by maximum junction temperature.
② Surface Mounted on FR4 Board, t ≤ 10 sec.
③ Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
④ Guaranteed by design, not subject to production
⑤ EAS condition: Tj=25℃,V_{DD}=15V,V_G=10V,L=0.5mH,Rg=25Ω

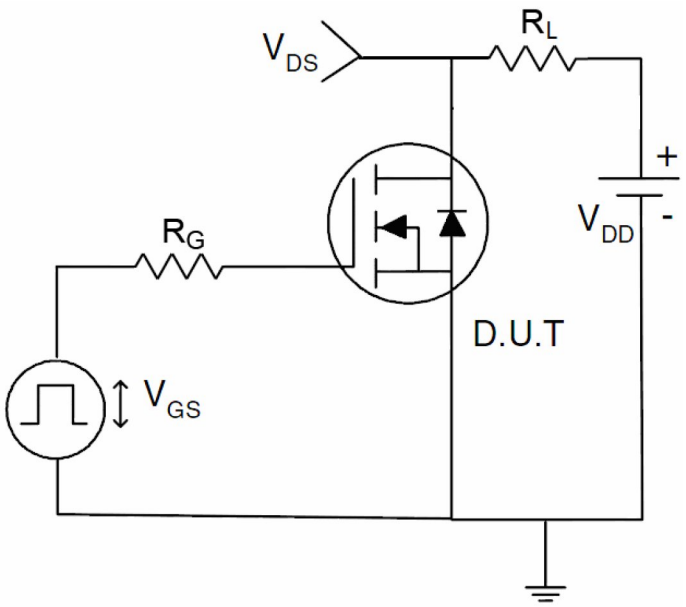
Test circuit



EAS test Circuit



Gate charge test Circuit



Switch Time Test Circuit

Typical Electrical and Thermal Characteristics (Curves)

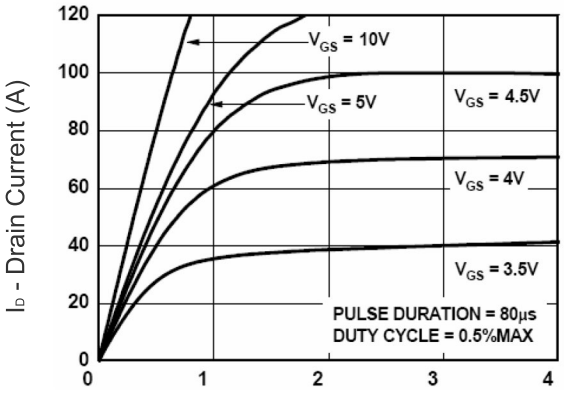


Figure 1 Output Characteristics

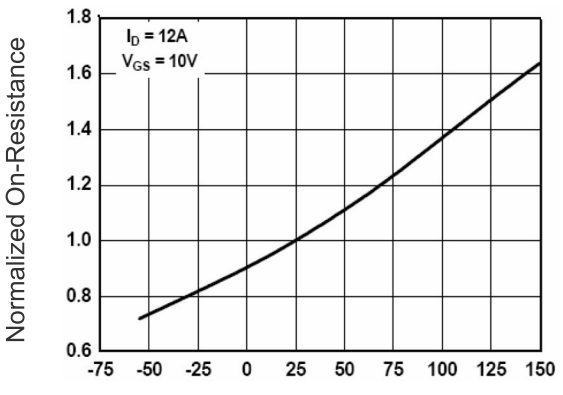


Figure 4 Rdson-Junction Temperature

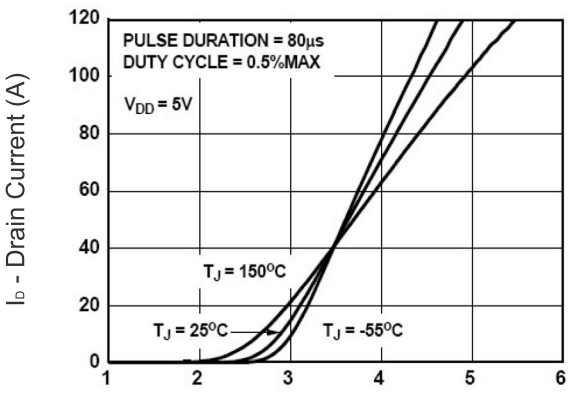


Figure 2 Transfer Characteristics

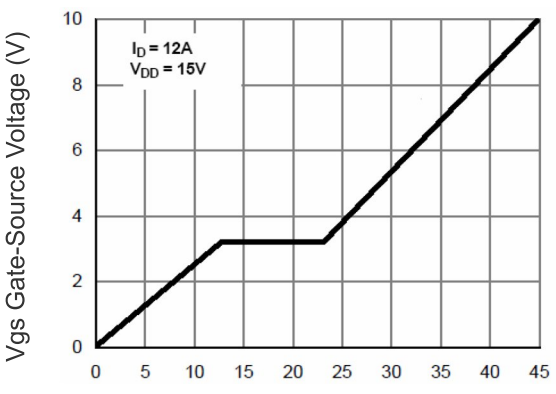


Figure 5 Gate Charge

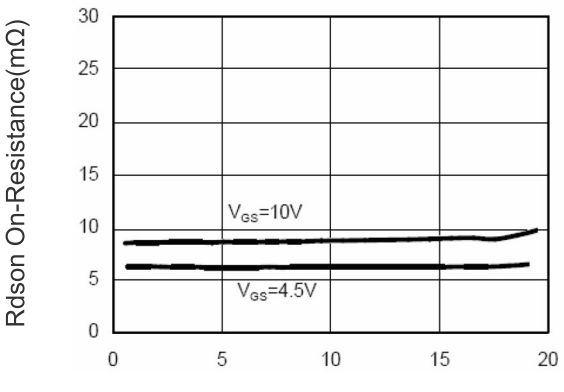


Figure 3 Rdson- Drain Current

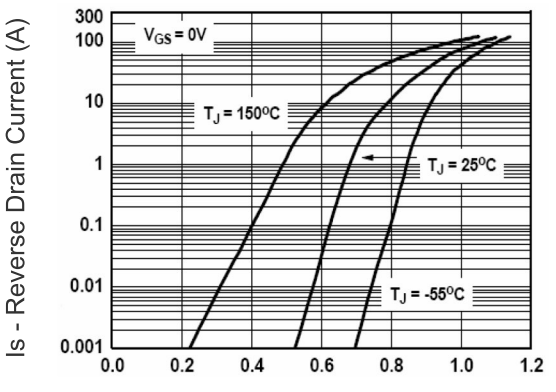


Figure 6 Source- Drain Diode Forward

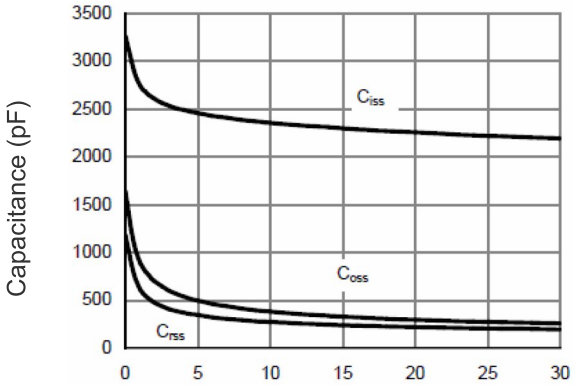


Figure 7 Capacitance vs Vds

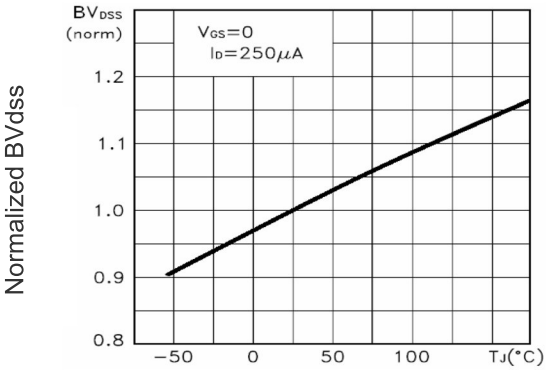


Figure 9 BV_{DSS} vs Junction Temperature

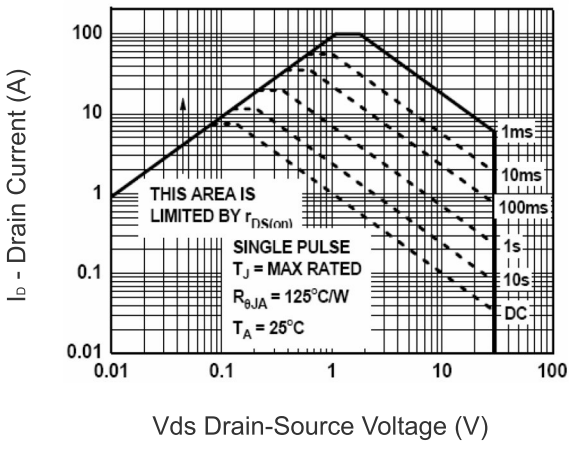


Figure 8 Safe Operation Area

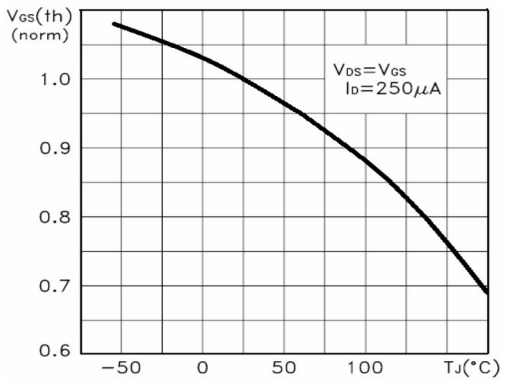


Figure 10 $V_{GS(th)}$ vs Junction Temperature

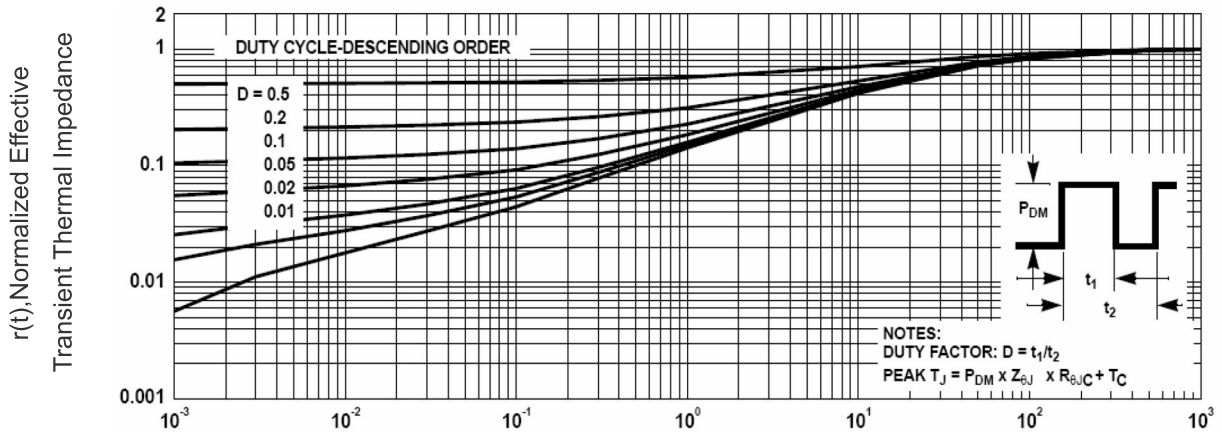
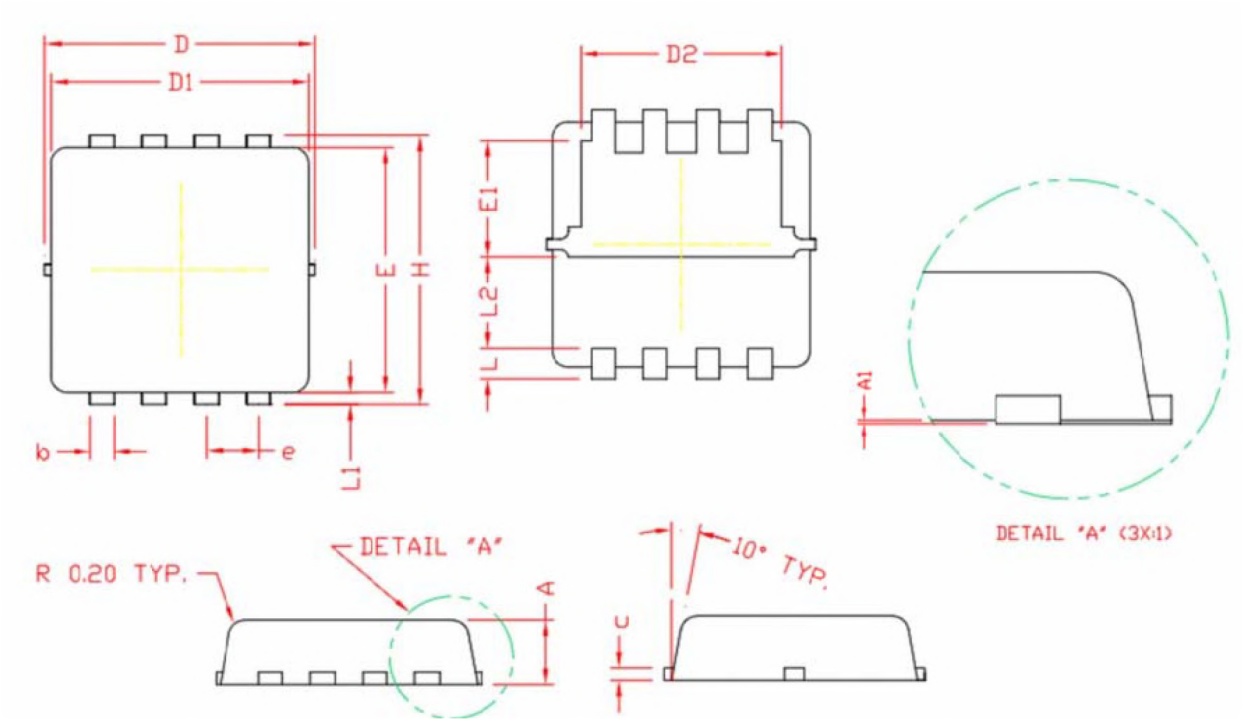


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN3X3 EP Package Information



COMMON DIMENSIONS

(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.70	0.80	0.90
A1	0.00	0.03	0.05
b	0.24	0.30	0.35
c	0.10	0.15	0.20
D	3.25	3.32	3.40
D1	3.05	3.15	3.25
D2	2.40	2.50	2.60
E	3.00	3.10	3.20
E1	1.35	1.45	1.55
e	0.65 BSC.		
H	3.20	3.30	3.40
L	0.30	0.40	0.50
L1	0.10	0.15	0.20
L2	1.13 REF.		

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